

# **N-Channel Power MOSFET**

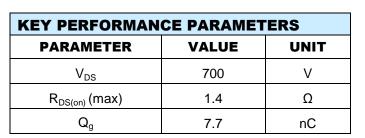
700V, 3.3A, 1.4Ω

#### **FEATURES**

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

# APPLICATION

- Power Supply
- Lighting





Sourd Pin 3

TO-251 (IPAK) T



Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>c</sub> = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	700	V
Gate-Source Voltage		$V_{GS}$	±30	V
Continuous Drain Current (Note 1)	$T_c = 25^{\circ}C$	- I <sub>D</sub>	3.3	A
	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 100^{\circ}{\rm C}$		2.0	
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	9.9	А
Total Power Dissipation @ $T_c = 25^{\circ}C$		P <sub>DTOT</sub>	38	W
Single Pulsed Avalanche Energy (Note 3)		E <sub>AS</sub>	64	mJ
Single Pulsed Avalanche Current (Note 3)		I <sub>AS</sub>	1.6	А
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	R <sub>eJC</sub>	3.3	°C/W
Junction to Ambient Thermal Resistance	R <sub>eja</sub>	62	°C/W

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air.

# **TSM70N1R4**



Taiwan Semiconductor

ELECTRICAL SPECIFICA	TIONS (T <sub>c</sub> = 25°C unles	ss otherwise no	oted)			
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 4)						•
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV <sub>DSS</sub>	700			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	2	3	4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1.2A$	R <sub>DS(ON)</sub>		0.9	1.4	Ω
Dynamic <sup>(Note 5)</sup>						•
Total Gate Charge		Qg		7.7		
Gate-Source Charge	$V_{DS} = 380V, I_{D} = 3.3A,$	Q <sub>gs</sub>		1.9		nC
Gate-Drain Charge	$V_{GS} = 10V$	Q <sub>gd</sub>		2.8		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C <sub>iss</sub>		370		_
Output Capacitance	f = 1.0MHz	C <sub>oss</sub>		34		pF
Gate Resistance	F = 1MHz, open drain	R <sub>g</sub>		3.4		Ω
Switching (Note 6)					•	
Turn-On Delay Time		t <sub>d(on)</sub>		14		
Turn-On Rise Time	$V_{DD} = 380V,$	t <sub>r</sub>		22		
Turn-Off Delay Time	$R_{GEN} = 25\Omega,$ $I_D = 3.3A, V_{GS} = 10V,$	t <sub>d(off)</sub>		24		ns
Turn-Off Fall Time		t <sub>f</sub>		20		
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_{\rm S} = 3.3$ A, $V_{\rm GS} = 0$ V	V <sub>SD</sub>			1.4	V
Reverse Recovery Time	$V_{R} = 200V, I_{S} = 2A$	t <sub>rr</sub>		163		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q <sub>rr</sub>		1		μC

#### Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. L = 50mH, I<sub>AS</sub> = 1.6A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 $\Omega$ , Starting T<sub>J</sub> = 25<sup>o</sup>C

4. Pulse test: PW  $\leq$  300µs, duty cycle  $\leq$  2%

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



### **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM70N1R4CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM70N1R4CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

Note:

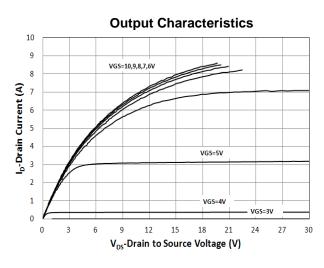
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

2. Halogen-free according to IEC 61249-2-21 definition

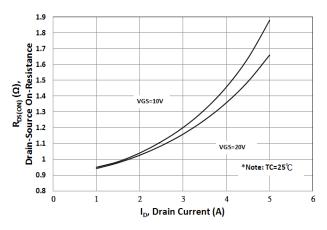


# **CHARACTERISTICS CURVES**

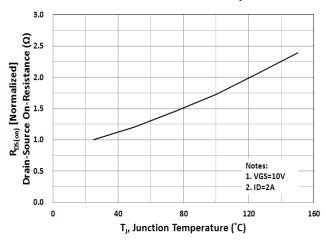
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

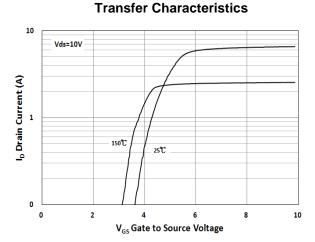


**On-Resistance vs. Drain Current** 

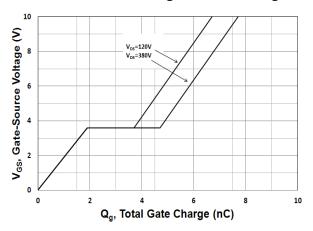


**On-Resistance vs. Junction Temperature** 

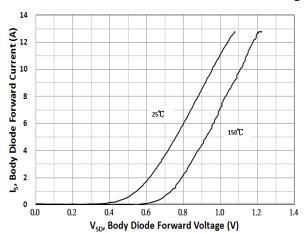




Gate-Source Voltage vs. Gate Charge



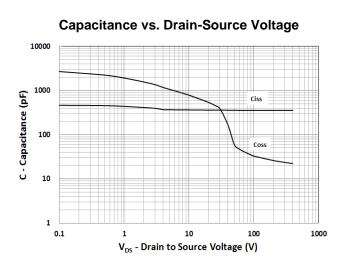
Source-Drain Diode Forward Current vs. Voltage



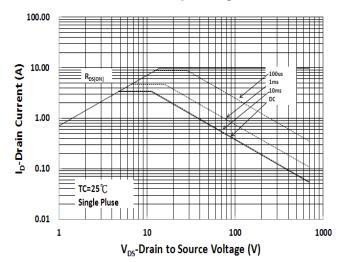


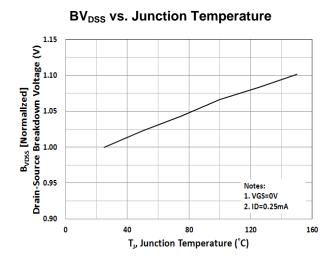
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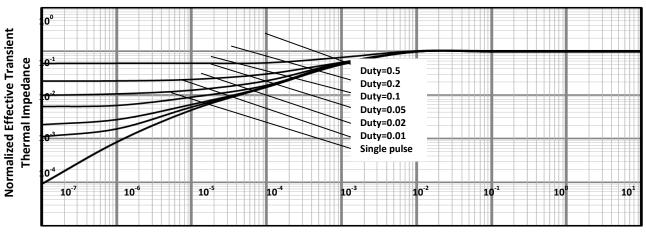


**Maximum Safe Operating Area** 





#### Normalized Thermal Transient Impedance

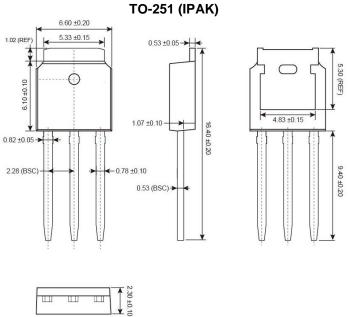




10<sup>1</sup>



# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



#### **MARKING DIAGRAM**

50	<ul><li>Y = Year Code</li><li>M = Month Code for Halogo</li></ul>	en Free Product
70N1R4 YML	<b>O</b> =Jan <b>P</b> =Feb	<b>Q</b> =Mar <b>R</b> =Apr
	<b>S</b> =May <b>T</b> =Jun	<b>U</b> =Jul <b>V</b> =Aug
	W =Sep X =Oct	Y =Nov Z =Dec
#1	<b>L</b> = Lot Code (1~9, A~Z)	

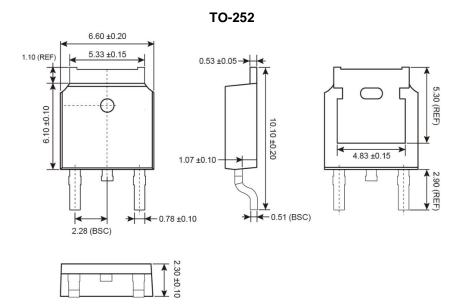




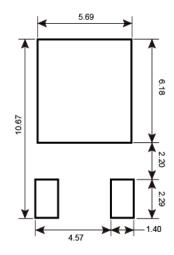
TAIWAN

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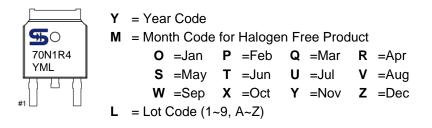
# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



## SUGGESTED PAD LAYOUT (Unit: Millimeters)



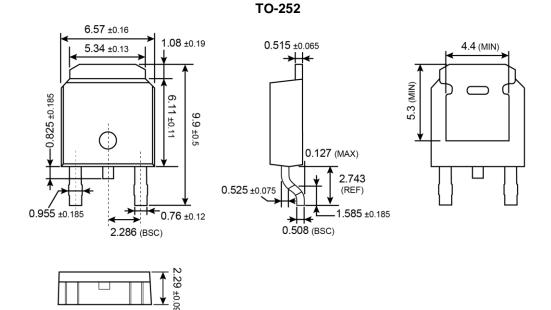
## **MARKING DIAGRAM**



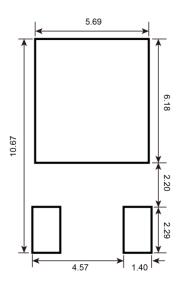




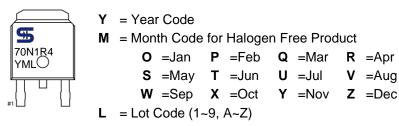
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### **MARKING DIAGRAM**





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